

UPDATED 07/25/2007

4.40-5.00 GHz 10-Watt Internally Matched Power FET

FEATURES

- 4.40–5.00GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +40.5 dBm Output Power at 1dB Compression
- 10.0 dB Power Gain at 1dB Compression
- 35% Power Added Efficiency
- -46 dBc IM3 at PO = 29.5 dBm SCL
- 100% Tested for DC, RF, and R_{TH}

ELECTRICAL CHARACTERISTICS (T_a = 25°C)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹		TYP	MAX	UNITS
P _{1dB}	Output Power at 1dB Compression $f = 4.40-5.00GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 3200\text{mA}$	39.5	40.5		dBm
G _{1dB}	Gain at 1dB Compression $f = 4.40-5.00GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 3200\text{mA}$	9.0	10.0		dB
ΔG	Gain Flatness $f = 4.40-5.00GHz$ $V_{DS} = 10 \text{ V}, I_{DSQ} \approx 3200\text{mA}$			±0.6	dB
PAE	Power Added Efficiency at 1dB Compression V_{DS} = 10 V, I_{DSQ} ≈ 3200mA f = 4.40-5.00GHz		35		%
Id _{1dB}	Drain Current at 1dB Compression f = 4.40-5.00GHz		3300	3800	mA
IM3	Output 3rd Order Intermodulation Distortion Δf = 10 MHz 2-Tone Test; Pout = 29.5 dBm S.C.L ² V_{DS} = 10 V, I_{DSQ} ≈ 65% IDSS f = 5.00GHz	-43	-46		dBc
I _{DSS}	Saturated Drain Current V _{DS} = 3 V, V _{GS} = 0 V		5800	6400	mA
V _P	Pinch-off Voltage V _{DS} = 3 V, I _{DS} = 60 mA		-2.5	-4.0	٧
R _{TH}	Thermal Resistance ³		2.5	3.0	°C/W

Note: 1. Tested with 50 Ohm gate resistor.

ABSOLUTE MAXIMUM RATING^{1,2}

SYMBOLS	PARAMETERS	CONTINUOUS ²	
3 TWIBOL3	FARAWETERS	CONTINUOUS	
Vds	Drain-Source Voltage	10V	
Vgs	Gate-Source Voltage	-4.5V	
lds	Drain Current	ldss	
lgsf	Forward Gate Current	120mA	
Pin	Input Power	@ 3dB Compression	
Tch	Channel Temperature	150 °C	
Tstg	Storage Temperature	-65 to +150 °C	
Pt	Total Power Dissipation	42W	

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

^{2.} S.C.L. = Single Carrier Level.

^{3.} Overall Rth depends on case mounting.



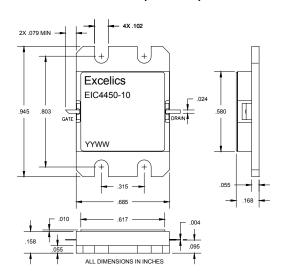
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PACKAGES OUTLINE

Dimensions in inches, Tolerance + .005 unless otherwise specified

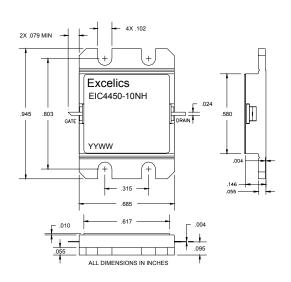
EIC4450-10 (Hermetic)





Caution! ESD sensitive device.

EIC4450-10NH (Non-Hermetic)





Caution! ESD sensitive device.

ORDERING INFORMATION

Part Number	Packages	Grade ¹	f _{Test} (GHz)	P _{1dB} (min)	IM ₃ (min) ²
EIC4450-10	Hermetic	Industrial	4.40-5.00GHz	39.5	-43
EIC4450-10NH	Non-Hermetic	Industrial	4.40-5.00GHz	39.5	-43

Notes:

- 1. Contact factory for military and hi-rel grades.
- 2. Exact test conditions are specified in "Electrical Characteristics" table.

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